

DOCKET NO: 245469US2DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
TADASHI IGUCHI, ET AL. : ATTN: APPLICATION DIVISION  
SERIAL NO: NEW U.S. APPLN. :  
FILED: HEREWITH :  
FOR: NONVOLATILE :  
SEMICONDUCTOR MEMORY :  
DEVICE AND ITS :  
MANUFACTURING METHOD :

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to a first examination on the merits, please amend the above-identified application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendments to the Claims** are reflected in the listing of claims which begins on page 3 of this paper.

**Remarks** begin on page 7 of this paper.